华润微电子（重庆）有限公司

CRSM060N06L2

SkyMOS2 N-MOSFET 63V, 5.3mΩ, 60A

Features

- Uses CRM(CQ) advanced SkyMOS2 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent Q_gx$R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

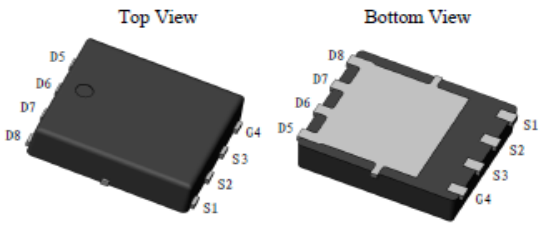
Product Summary

V_{DS}	63V
$R_{DS(on)@10V\ typ}$	5.3mΩ
$R_{DS(on)@4.5V\ typ}$	7.3mΩ
I_D	60A

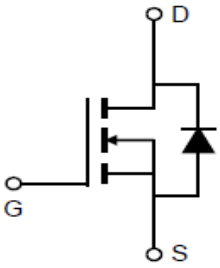
Applications

- Synchronous Rectification for AC/DC Quick Charger
- Battery management
- UPS (Uninterrupible Power Supplies)

100% Avalanche Tested



CRSM060N06L2



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRSM060N06L2	SM060N06L2	DFN5X6	Tape&Reel	N/A	N/A	5000pcs

Absolute Maximum Ratings

Parameter	**Symbol**	**Value**	**Unit**
Drain-source voltage	V_{DS}	63	V
Continuous drain current T_C = 25°C (Package limit) T_C = 25°C (Silicon limit) T_C = 100°C (Silicon limit)	I_D	 60 86 55	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	240	A
Avalanche energy, single pulse (L=0.3mH, Rg=25Ω)[1]	E_{AS}	63	mJ
Gate-Source voltage	V_{GS}	±20	V
Power dissipation (T_C = 25°C)	P_{tot}	78.1	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C

Notes:1.EAS was tested at Tj = 25℃, ID = 20.5A.

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Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case	R_{thJC}	1.60	°C/W
Thermal resistance, junction – ambient	R_{thJA}	47.0	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	63	-	-	V	V_{GS}=0V, I_D=250μA
Gate threshold voltage	$V_{GS(th)}$	1.2	1.7	2.2	V	V_{DS}=V_{GS},I_D=250μA
Zero gate voltage drain current	I_{DSS}	- -	0.02 -	1 10	μA	V_{DS}=60V,V_{GS}=0V T_j=25°C T_j=125°C
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=±20V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	-	5.3	6.4	mΩ	V_{GS}=10V, I_D=30A
		-	7.3	-		V_{GS}=4.5V, I_D=24A
			7.3	9.1		V_{GS}=5V, I_D=24A
Transconductance	g_{fs}	-	98	-	S	V_{DS}=5V,I_D=30A
Dynamic Characteristic						
Thermal change induce D-S voltage shift	DVDS	40	-	100	mV	V_{DS}=20V IM=10mA, ID=0.72A PT=10ms, DT=50μs
Input Capacitance	C_{iss}	-	1666	-	pF	V_{GS}=0V, V_{DS}=30V, f=1MHz
Output Capacitance	C_{oss}	-	510	-		
Reverse Transfer Capacitance	C_{rss}	-	34	-		
Gate Total Charge	Q_G	-	28	-	nC	V_{GS}=10V, V_{DS}=30V, I_D=30A, f=1MHz
Gate-Source charge	Q_{gs}	-	7.1	-		
Gate-Drain charge	Q_{gd}	-	4.3	-		
Turn-on delay time	$t_{d(on)}$	-	9.7	-	ns	V_{GS}=10V, V_{DD}=30V, R_{G_ext}=2.7Ω
Rise time	t_r	-	72	-		
Turn-off delay time	$t_{d(off)}$	-	24.8	-		
Fall time	t_f	-	87	-		
Gate resistance	R_G	-	2	-	Ω	V_{GS}=0V, V_{DS}=0V, f=1MHz

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Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.88	1	V	V_{GS}=0V,I_{SD}=30A
Body Diode Reverse Recovery Time	t_{rr}	-	27	-	ns	I_F=30A, dI/dt=300A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	-	49	-	nC	

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Typical Performance Characteristics

Fig 1: Output Characteristics

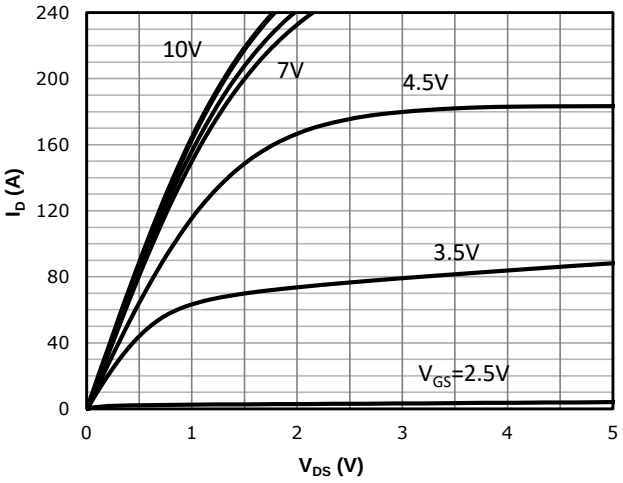


Fig 2: Transfer Characteristics

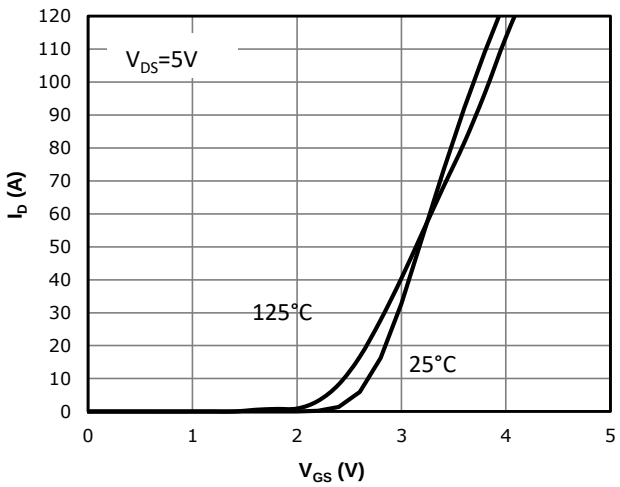


Fig 3: Rds(on) vs Drain Current and Gate Voltage

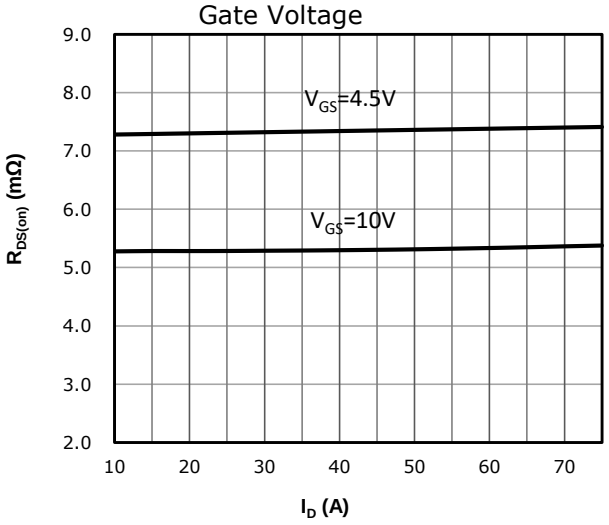


Fig 4: Rds(on) vs Gate Voltage

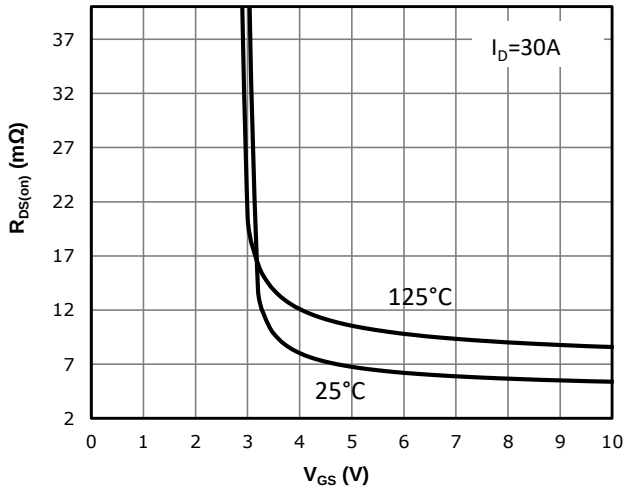


Fig 5: Rds(on) vs. Temperature

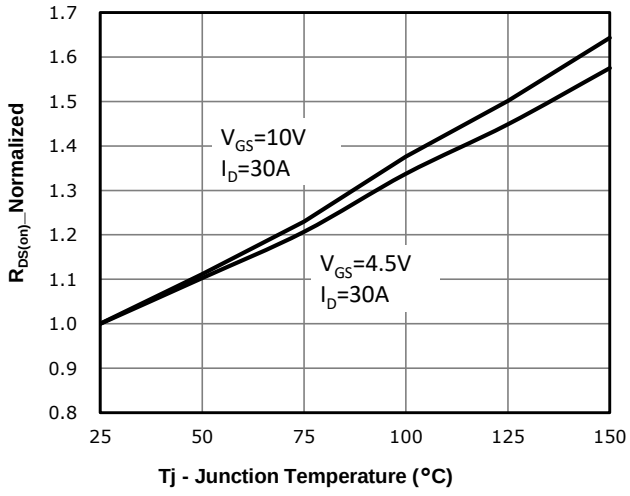
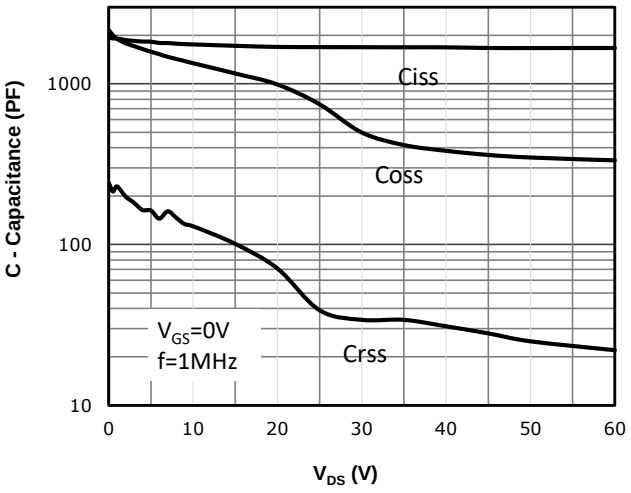


Fig 6: Capacitance Characteristics



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Fig 7: Gate Charge Characteristics

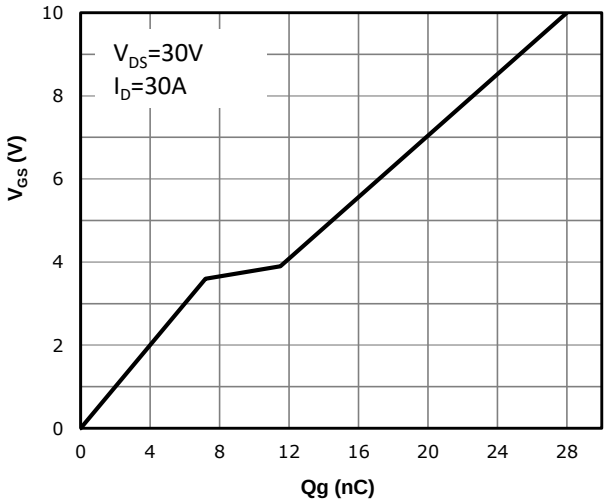


Fig 8: Body-diode Forward Characteristics

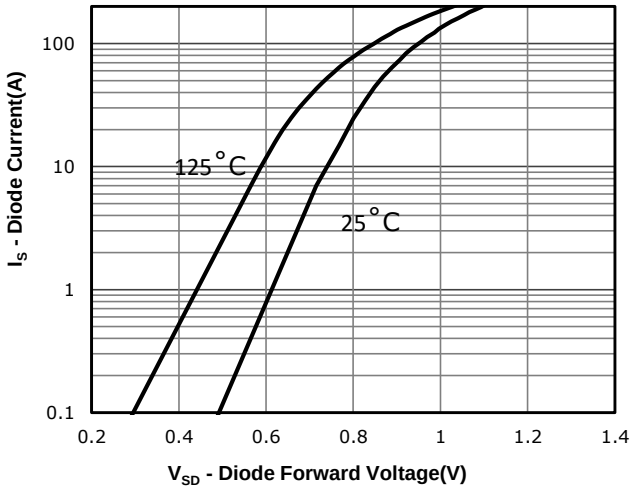


Fig 9: Power Dissipation

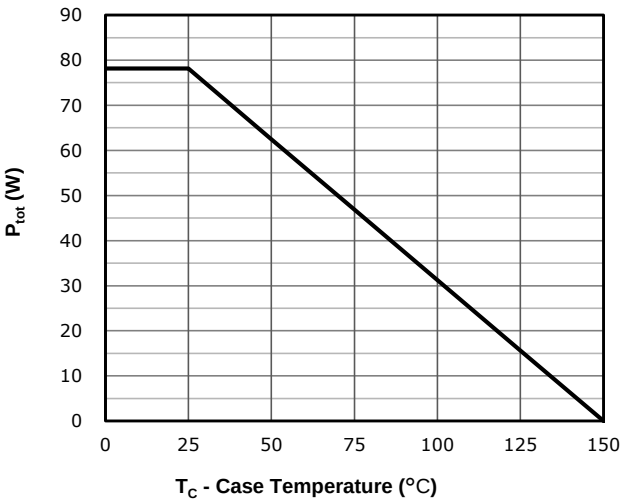


Fig 10: Drain Current Derating

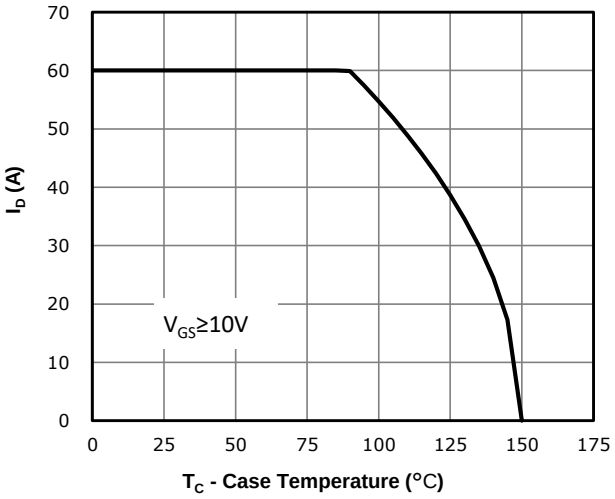


Fig 11: Safe Operating Area

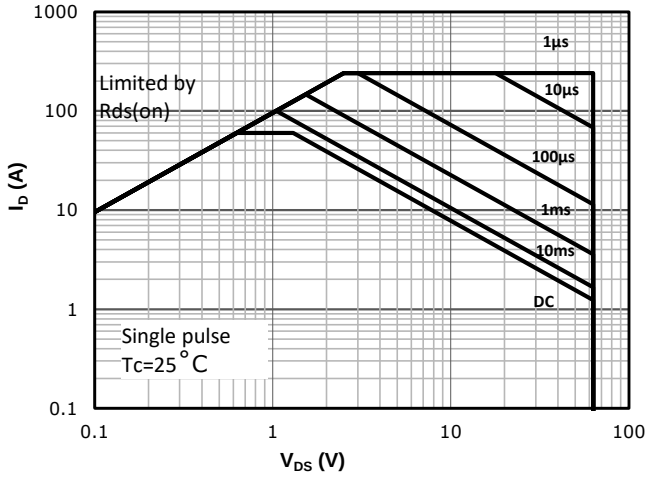
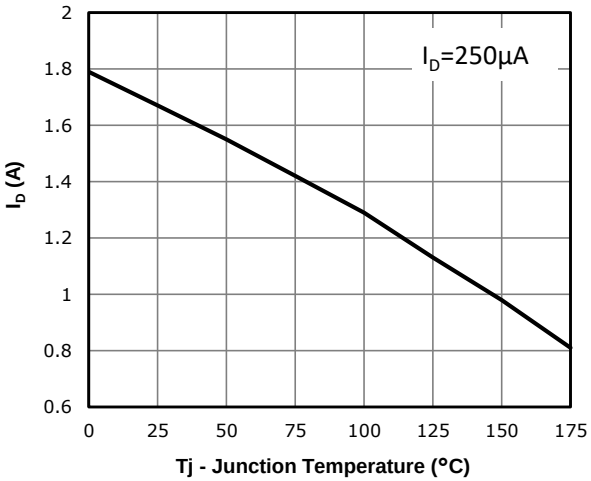
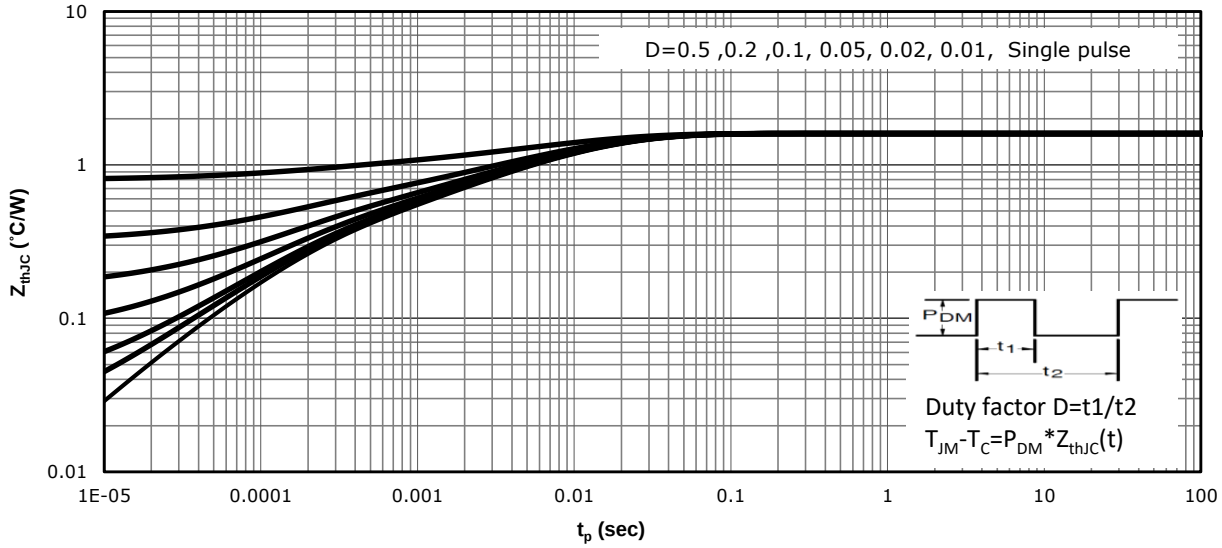


Fig 12: Vgs(th) vs. Temperature



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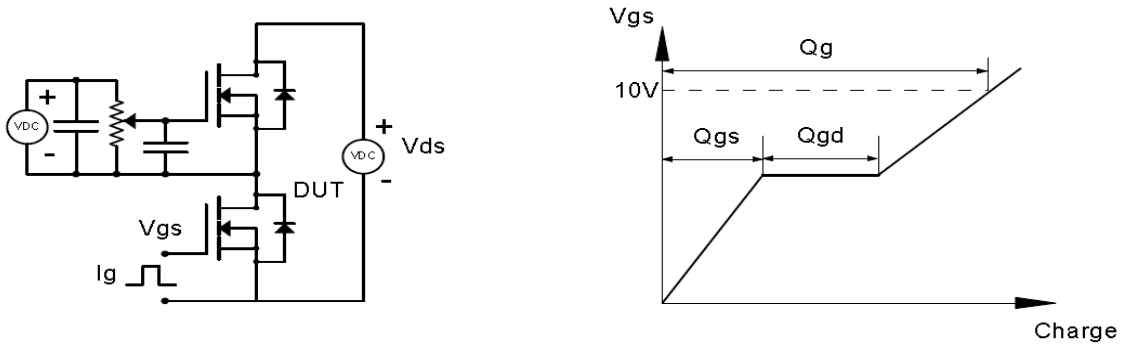
Fig 12: Max. Transient Thermal Impedance



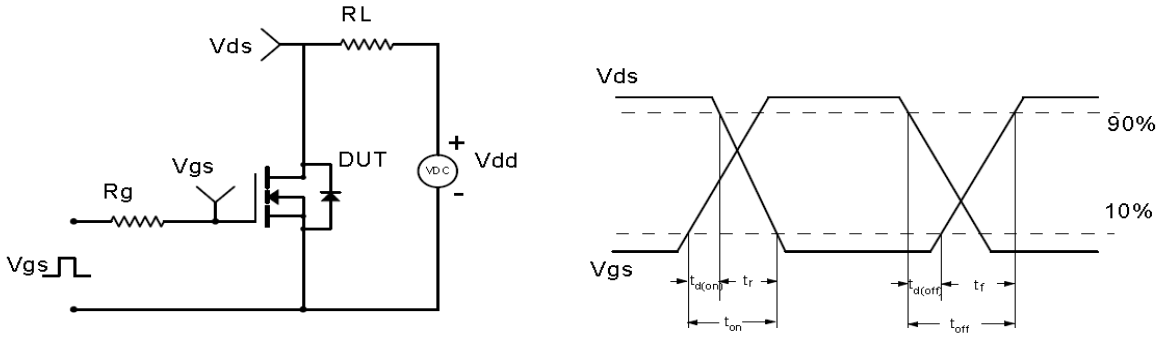
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Test Circuit & Waveform

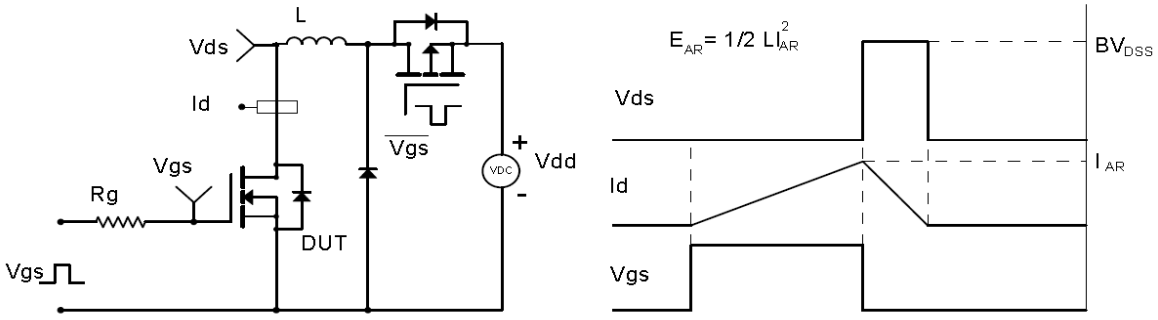
Gate Charge Test Circuit & Waveform



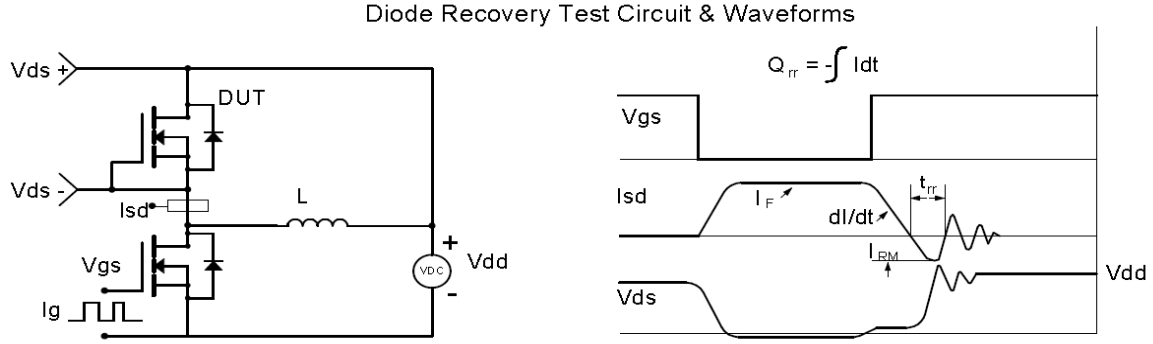
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

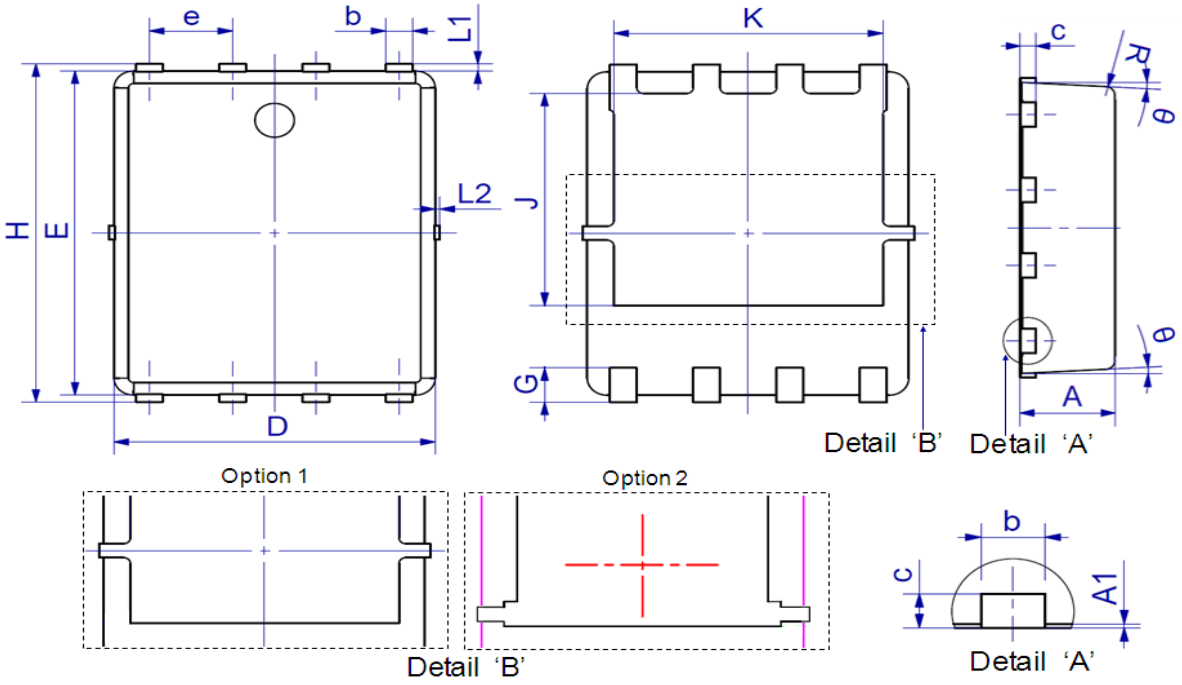


Diode Recovery Test Circuit & Waveforms



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Package Outline: DFN5X6



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.80	1.20	0.031	0.047
A1	0.00	0.05	0.000	0.002
b	0.30	0.51	0.012	0.020
c	0.15	0.35	0.006	0.014
D	4.80	5.40	0.189	0.213
e	1.27 BSC		0.050 BSC	
E	5.66	6.06	0.223	0.239
G	0.30	0.71	0.012	0.028
H	5.90	6.35	0.232	0.250
J	3.32	3.92	0.131	0.154
K	3.61	4.25	0.142	0.167
L1	0.05	0.25	0.002	0.010
L2	0.00	0.15	0.000	0.006
R	0.25 REF		0.010 REF	
θ	0°	12°	0°	12°

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Revision History

Revison	Date	Major changes
1.0	2019/1/3	Release of formal version.
1.1	2019/5/13	BVDS minimum value change & outline size revise
2.0	2019/6/25	Igss ± Supplement
3.0	2023/6/30	Add DVDS&RDS$_{(on)}$@5V,RthJL modified to RthJC
4.0	2024/9/5	Add Fig 12: Vgs(th) vs. Temperature

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

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